

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-2. (Cancelled)

~~2~~ ³ (Currently Amended) The method of Claim ~~2~~ 18, wherein the thin film is applied to the front surface of the semiconductor wafer.

~~3~~ ⁴ (Currently Amended) The method of Claim ~~4~~ +18 wherein the thin film comprises a film of dry photosensitive resin.

~~4~~ ⁵ (Original) The method of Claim 4, wherein the thin film is of the type known commercially by the name RISTON™.

6-7. (Cancelled)

~~5~~ ⁸ (Currently Amended) The method of Claim ~~4~~ +18, wherein the micro-mechanism comprises an electrostatic micro-actuator used for the fine positioning of a reading/writing transducer in a hard-disk reading/writing unit.

9. (Cancelled)

~~6~~ ¹⁰ (Currently Amended) The method of Claim ~~9~~ +18, wherein forming the hard-mask comprises depositing a layer of silicon dioxide or aluminum on the thin-dry film at low temperature and selectively removing the sacrificial layer comprises selectively removing the silicon dioxide or aluminum layer by a photolithographic technique.

11. (Cancelled)

~~12~~ 12. (Currently Amended) The method of Claim 11 ~~22~~, further comprising the mounting of a respective reading/writing transducer on each die.

~~13~~ 13. (Currently Amended) The method of Claim 10 ~~18~~, further comprising, after the definition of the electrical connection elements gluing a respective reading/writing transducer onto each micro-actuator component and soldering terminals of the transducer to the electrical connection elements of the respective micro-actuator micro-mechanism, and then dividing the semiconductor wafer with the transducers mounted by cutting it into a plurality of individual dice.

14-17. (Cancelled)

~~18~~ 18. (Currently Amended) A method of producing suspended elements between two portions of a micro-mechanism containing components that move relative to one another on a semiconductor wafer, the method comprising:

applying the adhesive side of a dry film over the micro-mechanism on the semiconductor wafer to immobilize the moveable components without penetrating any cavities therein;

forming a mask on the dry film;

depositing, developing, and selectively removing a sacrificial layer from the mask and the dry film to form windows on the dry film, the dry film protecting the cavities from infiltration of liquids during the developing step;

opening the windows by selectively etching the dry film;

depositing a dielectric layer to cover the windows without penetrating any underlying cavities;

depositing a conductive layer that is attached to at least one moveable portion of the micro-mechanism; and

selectively removing the conductive layer and the dielectric layer, and removing the dry film to form electrical connection elements suspended between the two portions of the micro-mechanism containing components that move relative to one another.

8 ~~19~~. (Original) The method of Claim 18, wherein applying the adhesive side of a dry film further comprises reducing the thickness of the wafer after the dry film has been applied.

9 ~~20~~. (Original) The method of Claim 18, wherein applying the adhesive side of a dry film comprises a subsequent step of applying a second adhesive layer to a back surface of the semiconductive wafer, the second adhesive layer having an exposed adhesive surface.

P ~~21~~. (Original) The method of Claim 18, further comprising removing the dry film to release the moveable components.

A ~~22~~. (Original) The method of Claim 21, further comprising, after selectively removing the conductive layer and the dielectric layer and before removing the dry film:

dividing the wafer into dice;
attaching a slider to each die;
gluing the die and the attached slider to a gimbal; and
attaching wires to the die.

L3 ~~23~~. (Original) The method of Claim 21, wherein removing the dry film comprises removing the dry film by oxygen plasma etching.

14 ~~24~~. (Original) The method of Claim 21, wherein removing the dry film comprises removing the dry film by immersion in a bath of NaOH.